

## **Amendment to the Specification:**

On page 1, please add the following paragraph beginning line 6:

This application claims the benefit of priority to German patent application no. DE 10219115.8, filed April 29, 2002.

On page 1, please replace the paragraph beginning line 6 with the following amended paragraph:

### **TECHNICAL FIELD**

The invention relates to a method for filling a contact hole, in which a covering layer is deposited in the contact hole, which covering layer contains a nitride as main constituent.

On page 1, please replace the paragraph beginning line 26 with the following amended paragraph:

### **SUMMARY**

It is an object of the invention to specify a simple method for filling a contact hole which, in particular, ensures reliable contact connection and a low contact resistance. Moreover, the intention is to specify an associated integrated circuit arrangement.

On page 6, please replace the paragraph beginning line 31 with the following amended paragraph:

### **Brief Description Of The Drawings**

The invention is explained below with reference to the accompanying figures, in which:

On page 7, please replace the paragraph beginning line 14 with the following amended paragraph:

**Detailed Description**

Figure 1 shows an integrated circuit arrangement 10 during production. In a semiconductor substrate (not illustrated) of the integrated circuit arrangement 10, a multiplicity of electrical components such as transistors have already been fabricated, e.g. in accordance with CMOS technology, in accordance with BICMOS technology or in accordance with a technology for power switching elements (power devices). The production was then continued until the application of a metal layer 12.